

$BV_{CES}$	430±30V
$I_C$	20A
$V_{CE(sat)}$ (Typ.)	1.6V
$E_{AS}$	250mJ

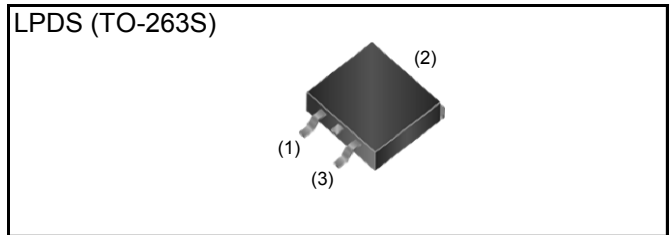
### ●Features

- 1) Low Collector - Emitter Saturation Voltage
- 2) High Self-Clamped Inductive Switching Energy
- 3) Built in Gate-Emitter Protection Diode
- 4) Built in Gate-Emitter Resistance
- 5) Qualified to AEC-Q101
- 6) Pb - free Lead Plating ; RoHS Compliant

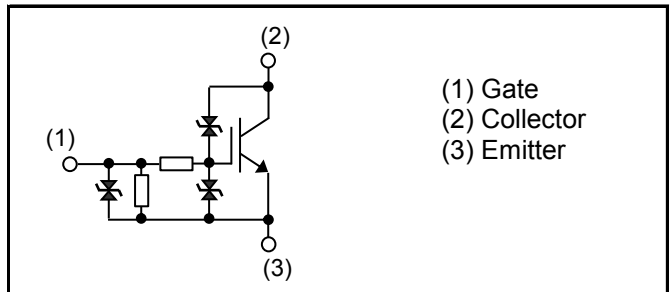
### ●Applications

- Ignition Coil Driver Circuits
- Solenoid Driver Circuits

### ●Outline



### ●Inner Circuit



### ●Packaging Specifications

Type	Packaging	Taping
	Reel Size (mm)	330
	Tape Width (mm)	24
	Basic Ordering Unit (pcs)	1,000
	Packing Code	TL
	Marking	RGPR20NS43

### ●Absolute Maximum Ratings (at $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit	
Collector - Emitter Voltage	$V_{CES}$	460	V	
Emitter-Collector Voltage ( $V_{GE} = 0V$ )	$V_{EC}$	25	V	
Gate - Emitter Voltage	$V_{GES}$	±10	V	
Collector Current	$I_C$	20	A	
Avalanche Energy (Single Pulse)	$T_j = 25^\circ\text{C}$	$E_{AS}$	250	mJ
	$T_j = 150^\circ\text{C}$	$E_{AS}^{*2}$	150	mJ
Power Dissipation	$P_D$	107	W	
Operating Junction Temperature	$T_j$	-40 to +175	$^\circ\text{C}$	
Storage Temperature	$T_{stg}$	-55 to +175	$^\circ\text{C}$	

### ●Thermal Resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	1.40	°C/W

### ●Electrical Characteristics (at $T_j = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector - Emitter Breakdown Voltage	$BV_{CES}$	$I_C = 2\text{mA}, V_{GE} = 0\text{V}$ $T_j = 25^\circ\text{C}$	400	430	460	V
		$T_j = -40 \text{ to } 175^\circ\text{C}^{*2}$	395	-	465	V
Emitter - Collector Breakdown Voltage	$BV_{EC}$	$I_C = -10\text{mA}, V_{GE} = 0\text{V}$	25	35	-	V
Gate - Emitter Breakdown Voltage	$BV_{GES}$	$I_G = \pm 5\text{mA}, V_{CE} = 0\text{V}$	$\pm 12$	-	$\pm 17$	V
Collector Cut - off Current	$I_{CES}$	$V_{CE} = 300\text{V}, V_{GE} = 0\text{V}$ $T_j = 25^\circ\text{C}$	-	-	7	$\mu\text{A}$
		$T_j = 150^\circ\text{C}^{*2}$	-	-	100	$\mu\text{A}$
Gate - Emitter Leakage Current	$I_{GES}$	$V_{GE} = \pm 10\text{V}, V_{CE} = 0\text{V}$	$\pm 0.4$	$\pm 0.6$	$\pm 1.2$	mA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$ $T_j = 25^\circ\text{C}$	1.3	1.7	2.1	V
		$T_j = 150^\circ\text{C}^{*2}$	-	1.3	-	V
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{A}, V_{GE} = 5\text{V}$ $T_j = 25^\circ\text{C}$	-	1.60	2.00	V
		$T_j = 150^\circ\text{C}$	-	1.80	-	V
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 4\text{A}, V_{GE} = 4.5\text{V}$ $T_j = 25^\circ\text{C}$	-	1.17	1.50	V
		$T_j = 150^\circ\text{C}$	-	1.13	-	V

●Electrical Characteristics (at  $T_j = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{A}, V_{GE} = 4\text{V}$ $T_j = 25^\circ\text{C}$	-	1.70	2.10	V
		$T_j = 150^\circ\text{C}$	-	1.90	-	V
Input Capacitance	$C_{ies}$	$V_{CE} = 10\text{V}$	-	1000	-	pF
Output Capacitance	$C_{oes}$	$V_{GE} = 0\text{V}$	-	175	-	
Reverse Transfer Capacitance	$C_{res}$	$f = 1\text{MHz}$	-	55	-	
Total Gate Charge	$Q_g$	$V_{CE} = 12\text{V}, I_C = 10\text{A},$ $V_{GE} = 5\text{V}$	-	14	-	nC
Turn - on Delay Time <sup>*1,*2</sup>	$t_{d(on)}$	$I_C = 8\text{A}, V_{CC} = 300\text{V},$ $V_{GE} = 5\text{V}, R_G = 100\Omega,$ $L = 5\text{mH}, T_j = 25^\circ\text{C}$	0.09	0.17	0.50	$\mu\text{s}$
Rise Time <sup>*1,*2</sup>	$t_r$		0.10	0.18	0.50	
Turn - off Delay Time <sup>*1,*2</sup>	$t_{d(off)}$		0.8	1.3	4.0	
Fall Time <sup>*1,*2</sup>	$t_f$		1.4	2.4	6.0	
Turn - on Delay Time <sup>*1</sup>	$t_{d(on)}$	$I_C = 8\text{A}, V_{CC} = 300\text{V},$ $V_{GE} = 5\text{V}, R_G = 100\Omega,$ $L = 5\text{mH}, T_j = 150^\circ\text{C}$	-	0.16	-	$\mu\text{s}$
Rise Time <sup>*1</sup>	$t_r$		-	0.23	-	
Turn - off Delay Time <sup>*1</sup>	$t_{d(off)}$		-	1.5	-	
Fall Time <sup>*1</sup>	$t_f$		-	3.9	-	
Avalanche Energy (Single Pulse)	$E_{AS}$	$L = 5\text{mH}, V_{GE} = 5\text{V},$ $V_{CC} = 30\text{V}, R_G = 1\text{k}\Omega,$ $T_j = 25^\circ\text{C}$	250	-	-	mJ
		$T_j = 150^\circ\text{C}^{*2}$	150	-	-	mJ
Gate Series Resistance	$R_G$		70	100	130	$\Omega$
Gate - Emitter Resistance	$R_{GE}$		8	16	24	k $\Omega$

\*1) Assurance items according to our measurement definition (Fig.18)

\*2) Design assurance items

●Electrical Characteristic Curves

Fig.1 Typical Output Characteristics

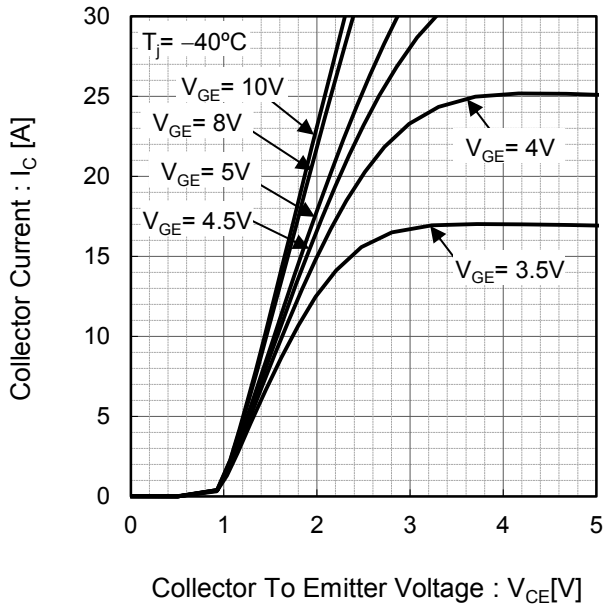


Fig.2 Typical Output Characteristics

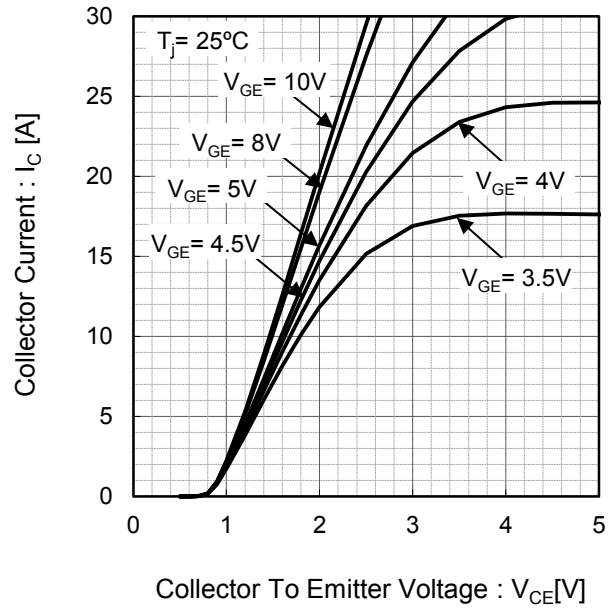


Fig.3 Typical Output Characteristics

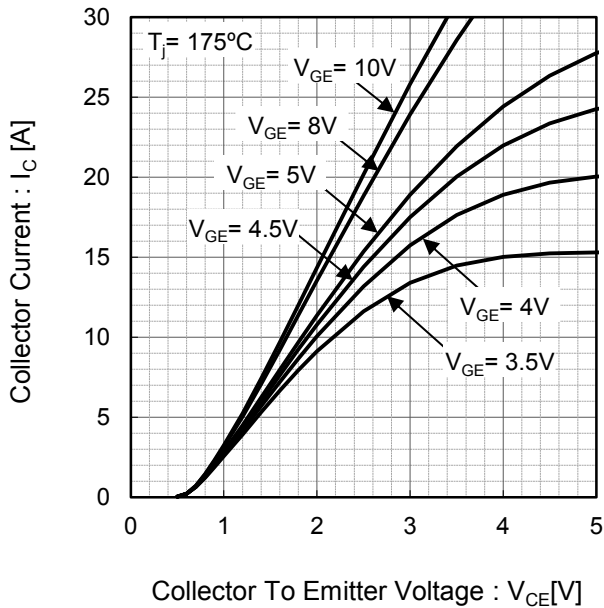
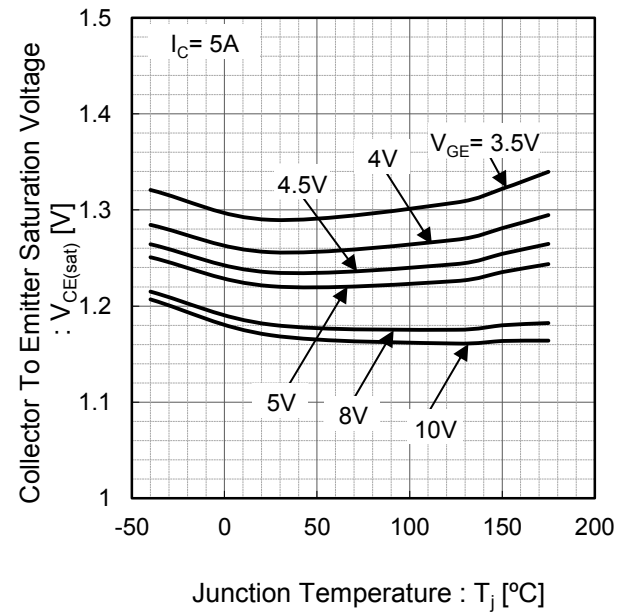


Fig.4 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



●Electrical Characteristic Curves

Fig.5 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature

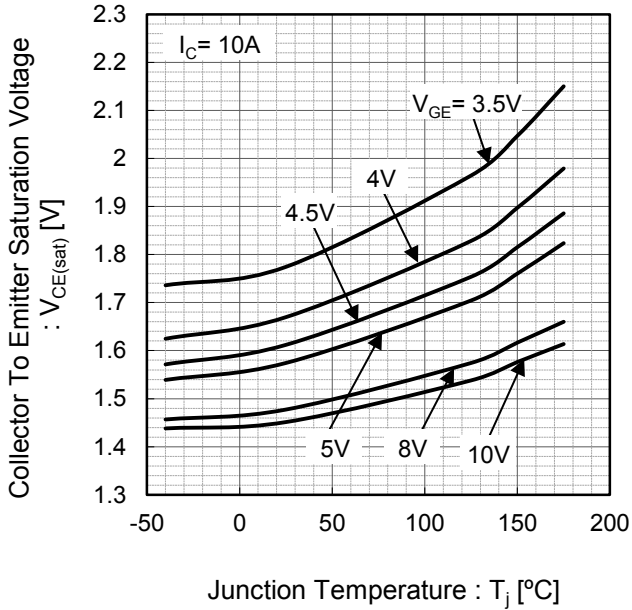


Fig.6 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature

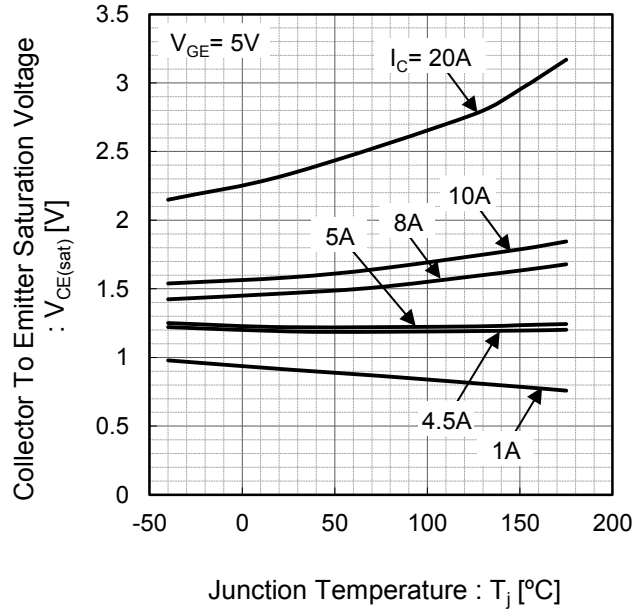


Fig.7 Typical Transfer Characteristics

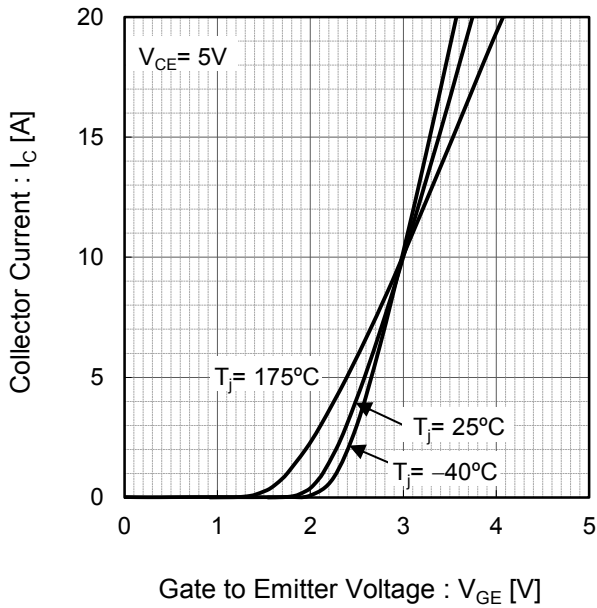
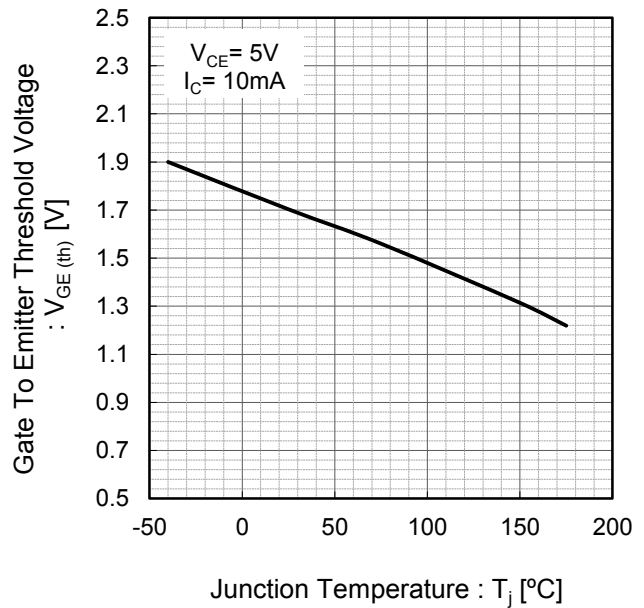


Fig.8 Typical Gate To Emitter Threshold Voltage vs. Junction Temperature



●Electrical Characteristic Curves

Fig.9 Typical Leakage Current vs. Junction Temperature

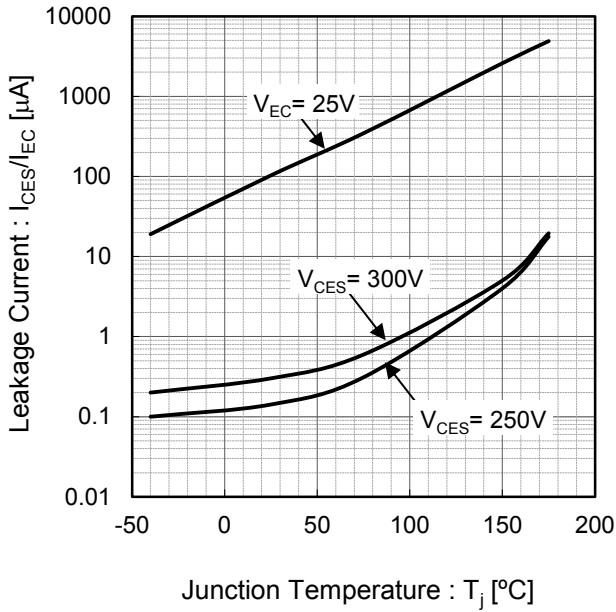


Fig.10 Typical Collector To Emitter Breakdown Voltage vs. Junction Temperature

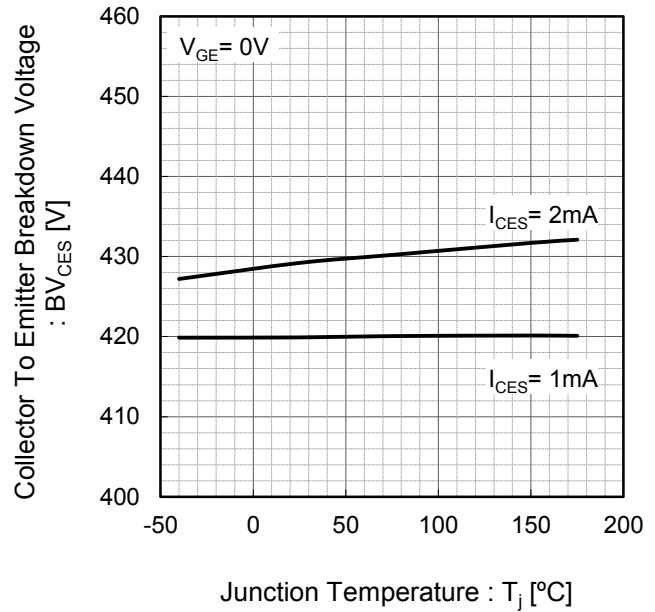


Fig.11 Typical Self Clamped Inductive Switching Current vs. Inductance

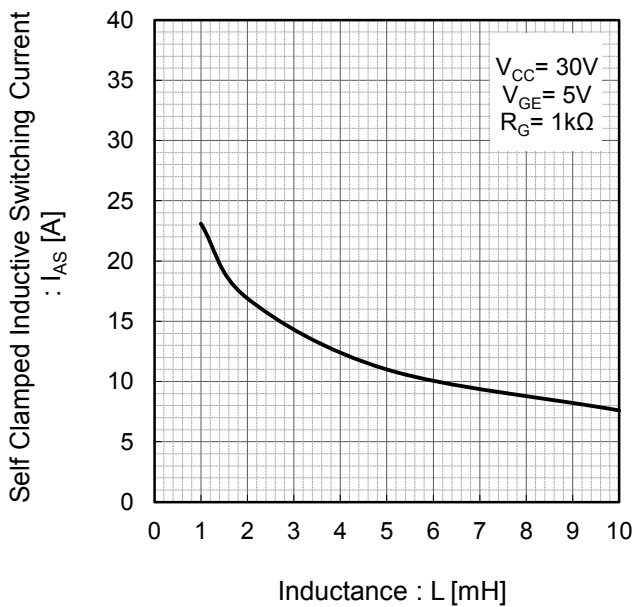
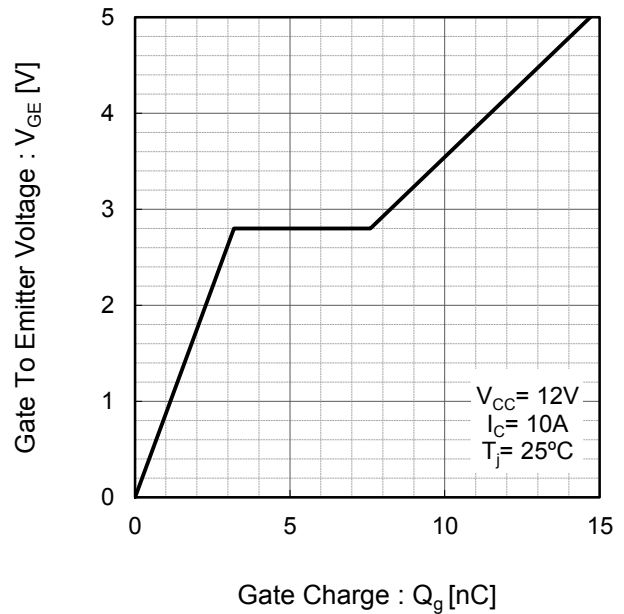


Fig.12 Typical Gate Charge



●Electrical Characteristic Curves

Fig.13 Typical Capacitance vs. Collector To Emitter Voltage

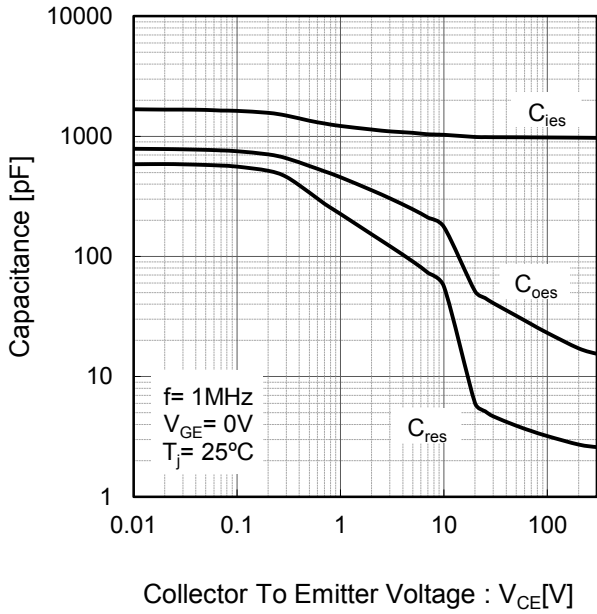


Fig.14 Typical Switching Time vs. Junction Temperature

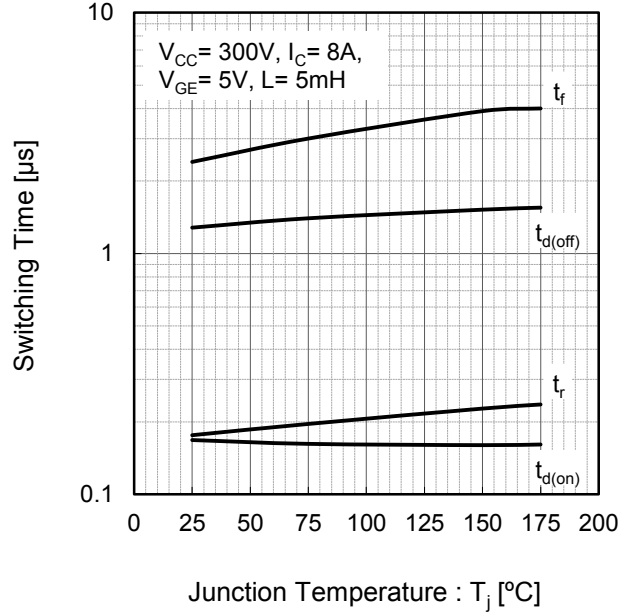
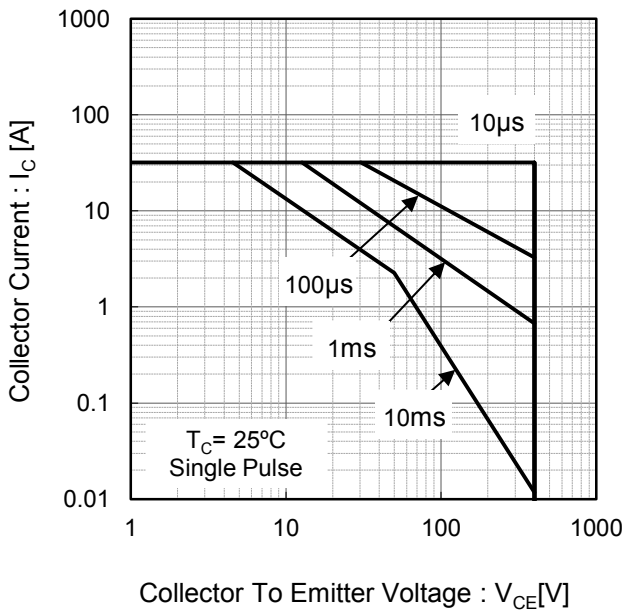
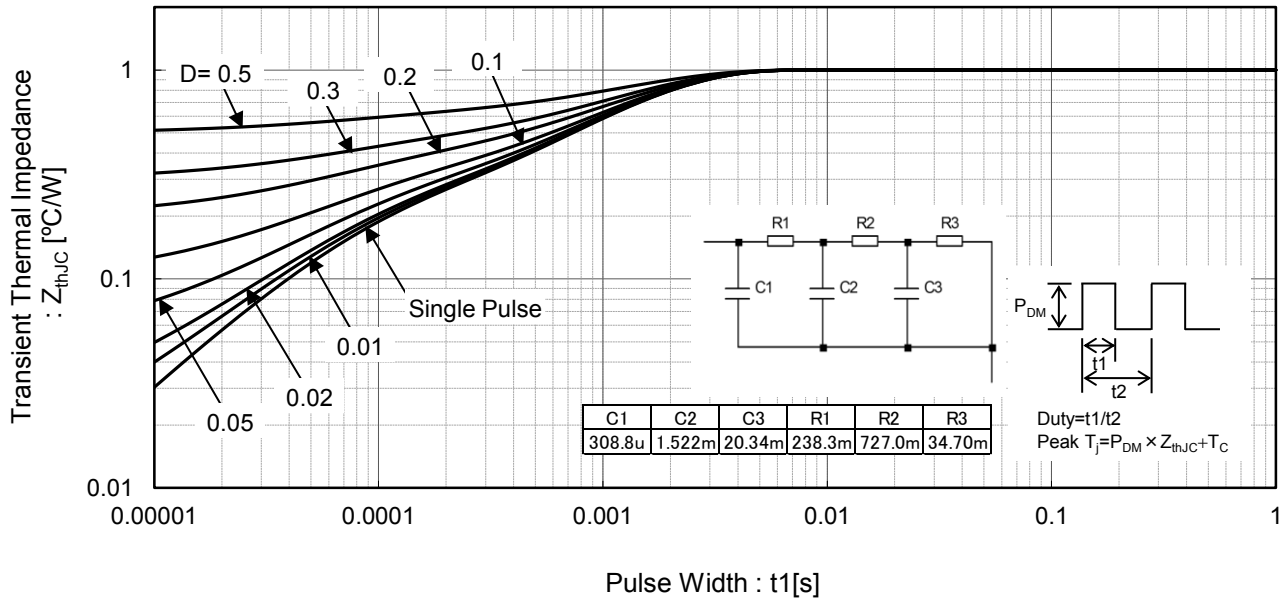


Fig.15 Forward Bias Safe Operating Area



●Electrical Characteristic Curves

Fig.16 Transient Thermal Impedance





●Inductive Load Switching Circuit and Waveform

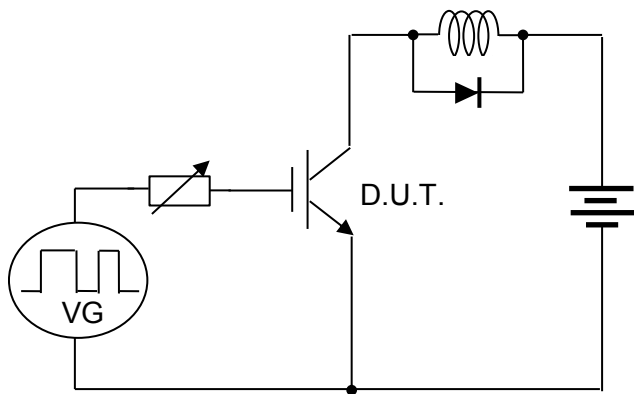


Fig.17 Inductive Load Switching Circuit

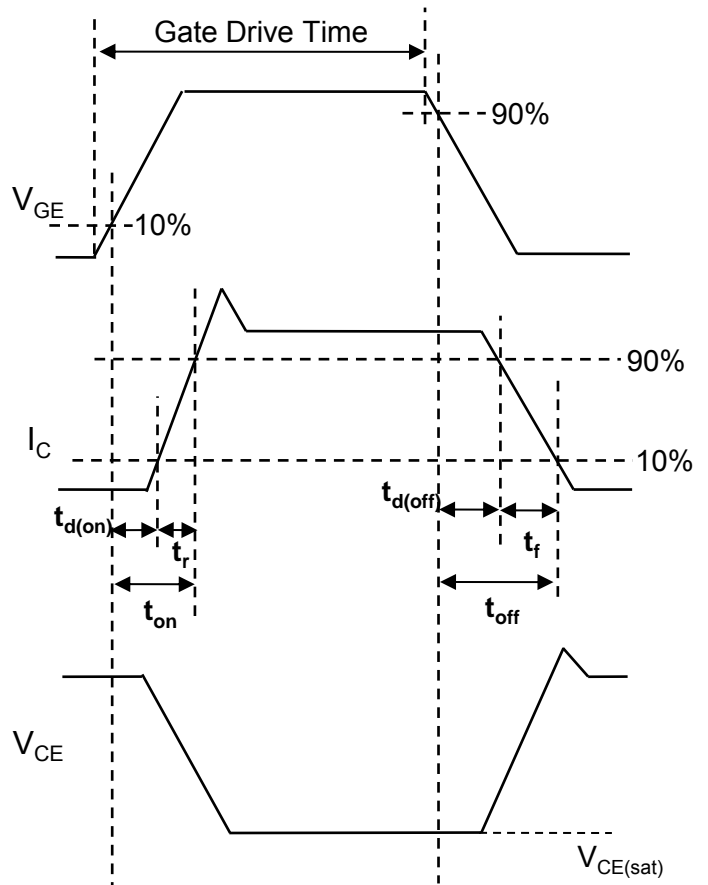


Fig.18 Inductive Load Switching Waveform

●Self Clamped Inductive Switching Circuit and Waveform

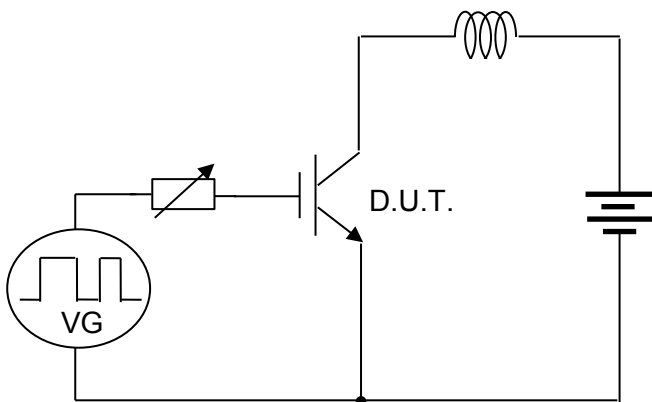


Fig.19 Self Clamped Inductive Switching Circuit

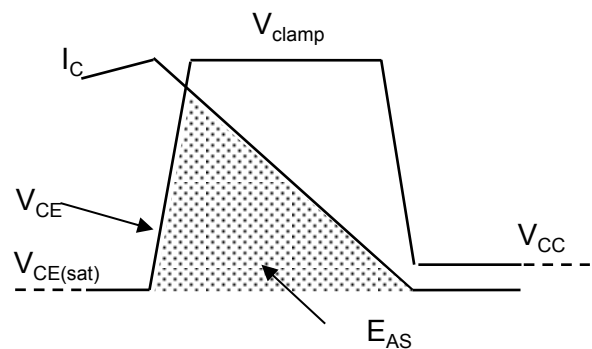


Fig.20 Self Clamped Inductive Switching Waveform

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Part Number	RGPR20NS43HR
Package	LPDS
Unit Quantity	1000
Minimum Package Quantity	1000
Packing Type	Taping
Constitution Materials List	inquiry
RoHS	Yes